

Development of X-ray detector using optical switching readout for high-speed imaging

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I. Introduction

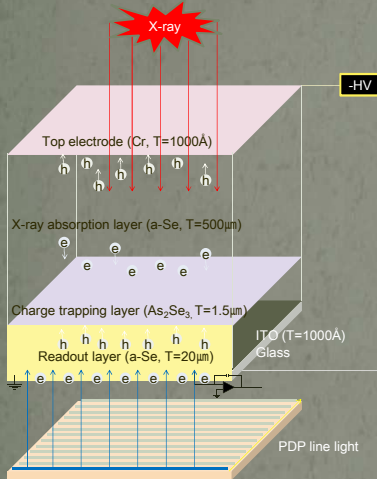
Objectives

- To solve electric noise in matrix circuit structure of TFT readout system.
- To enhance conversion efficiency in high definition of TFT readout.
- To obtain high X-ray conversion efficiency by using double-layer of a-Se.
- To obtain lower noise and high DQE in switching by light without TFT.
- To obtain image in high speed by electrical scanning of optical line light of 2D readout light source.

II. Performance & Fabrication

Operations

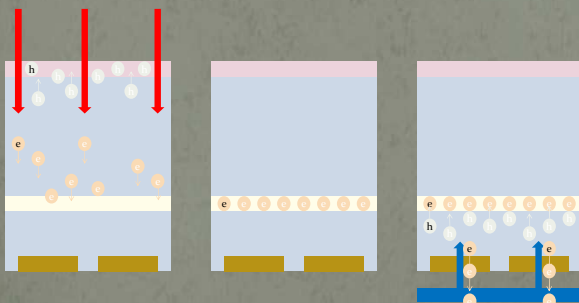
Schematic diagram



- Direct conversion & A-Se double layer & Direct optical switching
- Double layer of a-Se
 - High absorption of X-ray
- Switched by light without TFT
 - Low noise & High DQE

- X-ray absorption layer
 - X-ray exposure
 - Generation of free electron-hole pairs
 - Direct conversion of X-ray to electron
- Charge trapping layer
 - Accumulation of electrons
- Readout layer
 - Light exposure from linear optical source
 - Generation of free electron-hole pairs
 - Drift to accumulated electrons
 - Readout of electrons

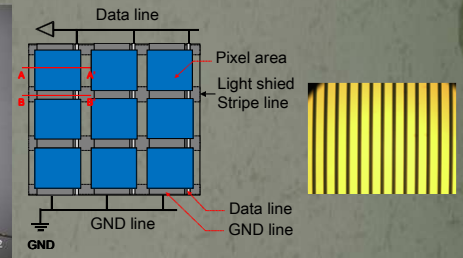
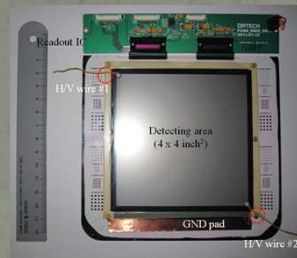
Imaging processes



- | | | |
|---|--|--|
| (a) Conversion | (b) Accumulation | (c) Readout |
| <ul style="list-style-type: none"> Conversion <ul style="list-style-type: none"> High negative voltage X-ray exposure Direct conversion of X-ray to electron | <ul style="list-style-type: none"> Accumulation <ul style="list-style-type: none"> Turn off of high negative voltage Charge distribution | <ul style="list-style-type: none"> Readout <ul style="list-style-type: none"> Light exposure Readout of electron |

Fabricated devices

X-ray sensor

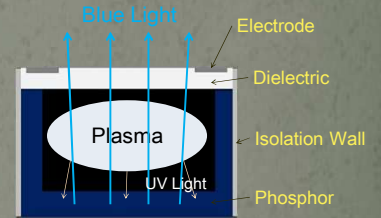
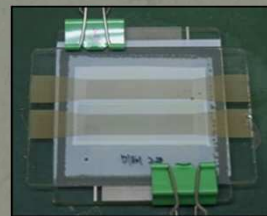


- X-ray sensor
 - 512 x 512
 - 200 x 200 µm
 - Charge storage : ETL(As₂Se₃)

Layout & Readout electrode

- Readout electrode patterning to enhance readout efficiency
- Opaque electrode : block the readout light
- Transparent electrode : readout path

PDP line light



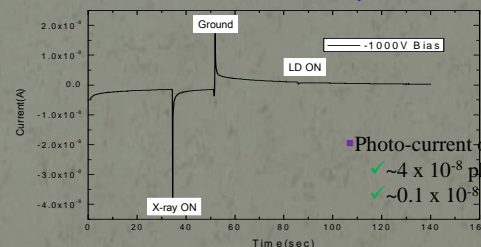
3-electrode AC PDP

- Ne-Xe dielectric barrier discharge
- Blue phosphor
- MgCaO protective layer
- Ray tracing technique
- 4 x 4 inch

III. Results and Discussions

Characteristic Measurements

Generated currents of X-ray sensor

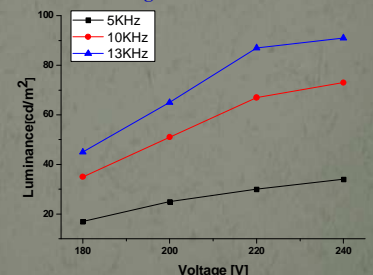


- Photo-current of X-ray sensor
 - $\sim 4 \times 10^{-8}$ photo-current by X-ray
 - $\sim 0.1 \times 10^{-8}$ photo-current by blue light

Luminance of PDP line light



- Luminance of line light
 - $\sim 30 \sim 90 \text{ cd/m}^2$



Conclusions & Future works

- Optical switching readout X-ray detector is developed.
- Optical line light can be operated to electrical scanning for high-speed imaging.
- X-ray imaging will be acquired by reducing electro-magnetic interference.